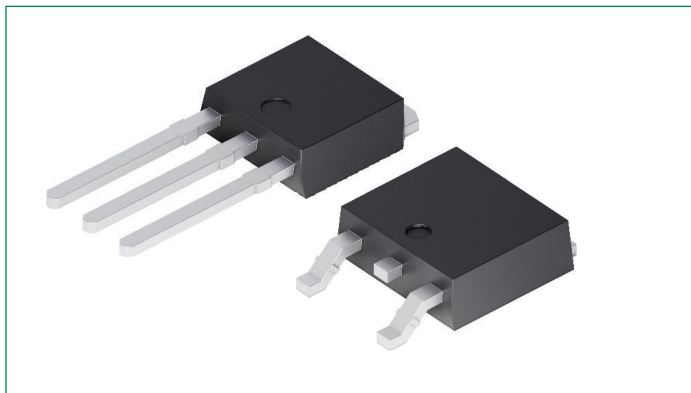


# MCR12DSM & MCR12DSN

## 100 V–600 V Surface Mount SCRs



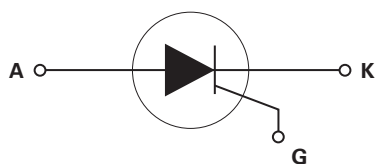
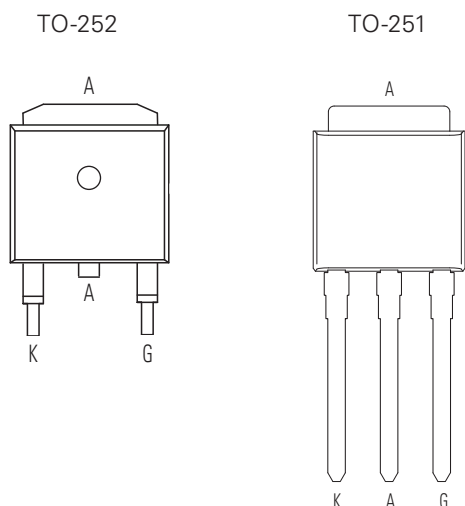
### Description

The MCR12DSM and MCR12DSN devices are designed for high-volume, low-cost industrial and consumer applications such as motor control, process control, temperature, light and speed control, Capacitive Discharge Ignition (CDI), and small engines.

### Features

- ESD Ratings: Human Body Model – 3B > 8000 V, Machine Model – C > 400 V
- UL Recognized compound meeting flammability rating V-0
- Low-level triggering and holding characteristics
- Passivated die surface for reliability and uniformity
- Small size

### Pinout Diagram



**K:** Cathode; **A:** Anode; **G:** Gate

### Product Summary

Characteristic	Value	Unit
$I_{T(RMS)}$	12	A
$V_{DRM}/V_{RRM}$	600 or 800	V
$I_{GT}$	200 or 300	mA

**Maximum Ratings** ( $T_{vj} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

Symbol	Characteristics	Conditions	Value	Units	
$V_{DRM}/V_{RRM}$	Repetitive Peak Off-state Voltage <sup>1</sup>	$T_{vj} = -40\text{ to }+110\text{ }^{\circ}\text{C}$ , Sine Wave, 50 to 60 Hz, $R_{GK} = 1\text{ k}\Omega$	MCR12DSM	600	V
			MCR12DSN	800	
$I_{T(RMS)}$	On-state RMS Current	180° Conduction Angles; $T_C = 75\text{ }^{\circ}\text{C}$	12	A	
$I_{T(AV)}$	Average On-state Current	180° Conduction Angles; $T_C = 75\text{ }^{\circ}\text{C}$	7.6	A	
$I_{TSM}$	Non-repetitive Surge Peak On-state Current	½ cycle, sine wave, 60 Hz, $T_{vj} = 110\text{ }^{\circ}\text{C}$	100	A	
$I^2t$	$I^2t$ Value for Fusing	$t_p = 8.3\text{ ms}$	41	A <sup>2</sup> s	
$P_{GM}$	Forward Peak Gate Power	$P_W \leq 1\text{ }\mu\text{s}$ , $T_C = 75\text{ }^{\circ}\text{C}$	5	A	
$P_{G(AV)}$	Average Gate Power Dissipation	$t_p = 8.3\text{ ms}$ , $T_C = 75\text{ }^{\circ}\text{C}$	0.5	W	
$I_{GM}$	Peak Gate Current	$P_W \leq 1\text{ }\mu\text{s}$ , $T_C = 75\text{ }^{\circ}\text{C}$	2	A	
$T_{stg}$	Storage Temperature Range	–	–40 to 150	°C	
$T_{vj}$	Virtual Junction Temperature Range	–	–40 to 110	°C	

Note 1:  $V_{DRM}$  and  $V_{RRM}$  for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the component are exceeded.

**Electrical Characteristics – OFF** ( $T_{vj} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

Symbol	Characteristics	Conditions	Min.	Typ.	Max.	Units	
$I_{DRM}/I_{RRM}$	Peak Repetitive Forward or Reverse Blocking Current <sup>2</sup>	$V_{AK} = \text{Rated } V_{DRM} \text{ or } V_{RRM}$ , $R_{GK} = 1.0\text{ k}\Omega$	$T_{vj} = 25\text{ }^{\circ}\text{C}$	–	–	10	$\mu\text{A}$
			$T_{vj} = 110\text{ }^{\circ}\text{C}$	–	–	500	

Note 2: Ratings apply for negative gate voltage or  $R_{GK} = 1.0\text{ k}\Omega$ . Devices shall not have a positive gate voltage concurrently with a negative voltage on the anode. Component should not be tested with a constant current source for forward and reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.

**Electrical Characteristics – ON** ( $T_{vj} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

Symbol	Characteristics	Conditions	Min.	Typ.	Max.	Units	
$V_{GRM}$	Peak Reverse Gate Blocking Voltage	$I_{GR} = 10\text{ }\mu\text{A}$	10	12.5	18	V	
$I_{GRM}$	Peak Reverse Gate Blocking Current	$V_{GR} = 10\text{ V}$	–	–	1.2	$\mu\text{A}$	
$V_{TM}$	Peak Forward On–State Voltage <sup>3</sup>	$I_{TM} = 20\text{ A}$	–	1.3	1.9	V	
$I_{GT}$	Gate Trigger Voltage <sup>4</sup>	$V_{AK} = 12\text{ V}_{dc}$ ; $R_L = 100\text{ }\Omega$ , $T_C = 110\text{ }^{\circ}\text{C}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$	5	12	200	$\mu\text{A}$
			$T_{vj} = -40\text{ }^{\circ}\text{C}$	–	–	300	
$V_{GT}$	Gate Trigger Voltage (continuous dc) <sup>4</sup>	$V_{AK} = 12\text{ V}$ ; $R_L = 100\text{ }\Omega$	$T_{vj} = 25\text{ }^{\circ}\text{C}$	0.45	0.65	1	V
			$T_{vj} = -40\text{ }^{\circ}\text{C}$	–	–	1.5	
			$T_{vj} = 110\text{ }^{\circ}\text{C}$	0.2	–	–	
$I_H$	Holding Current	$V_D = 12\text{ V}$ , Initiating Current = 200 mA, $R_{GK} = 1\text{ k}\Omega$	$T_{vj} = 25\text{ }^{\circ}\text{C}$	0.5	1	6	mA
			$T_{vj} = -40\text{ }^{\circ}\text{C}$	–	–	10	
$I_L$	Latching Current	$V_D = 12\text{ V}$ , $I_G = 2.0\text{ mA}$ , $R_{GK} = 1\text{ k}\Omega$	$T_{vj} = 25\text{ }^{\circ}\text{C}$	0.5	1	6	mA
			$T_{vj} = -40\text{ }^{\circ}\text{C}$	–	–	10	
$t_{gt}$	Turn-on Time (Source Voltage = 12 V, $R_S = 6.0\text{ k}\Omega$ , $I_T = 16\text{ A(pk)}$ , $R_{GK} = 1.0\text{ k}\Omega$ )	$V_D = \text{Rated } V_{DRM}$ , Rise Time = 20 ns, Pulse Width = 10 $\mu\text{s}$	–	2	5	$\mu\text{s}$	

Note 3: Pulse Test: Pulse Width  $\leq 2.0\text{ msec}$ , Duty Cycle  $\leq 2\%$ .

Note 4:  $R_{GK}$  current not included in measurement

## Thermal Characteristics

Symbol	Characteristics	Value	Units
$R_{th(j-c)}$	Thermal Resistance, Junction to Case	2.2	K/W
$R_{th(j-a)}$	Thermal Resistance, Junction to Ambient	88	
$R_{th(j-a)}$	Thermal Resistance, Junction to Ambient <sup>5</sup>	80	
$T_L$	Maximum Lead Temperature for Soldering Purposes <sup>6</sup>	260	°C

Note 5: These ratings are applicable when surface mounted on the minimum pad sizes recommended.

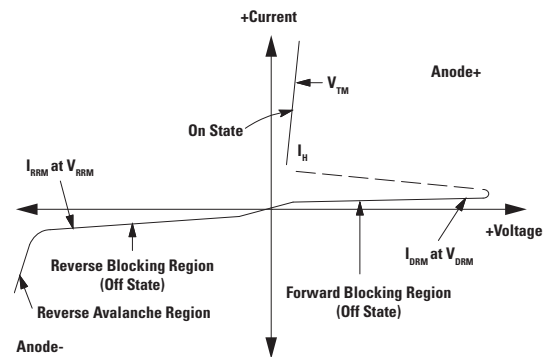
Note 6: 1/8" from case for 10 seconds

## Dynamic Characteristics

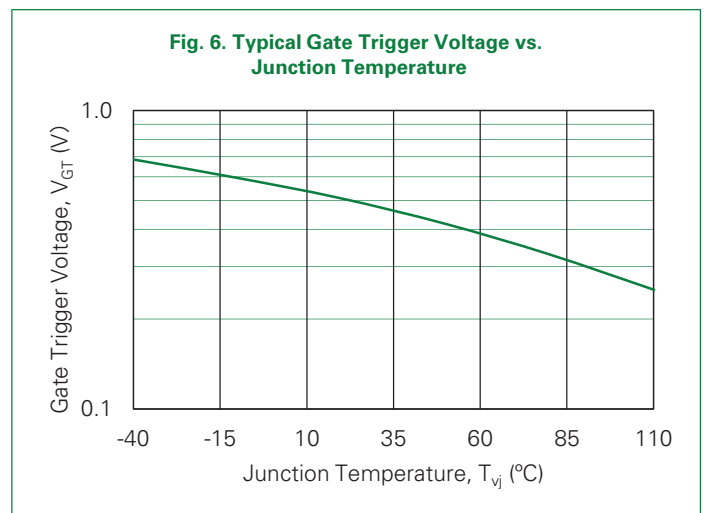
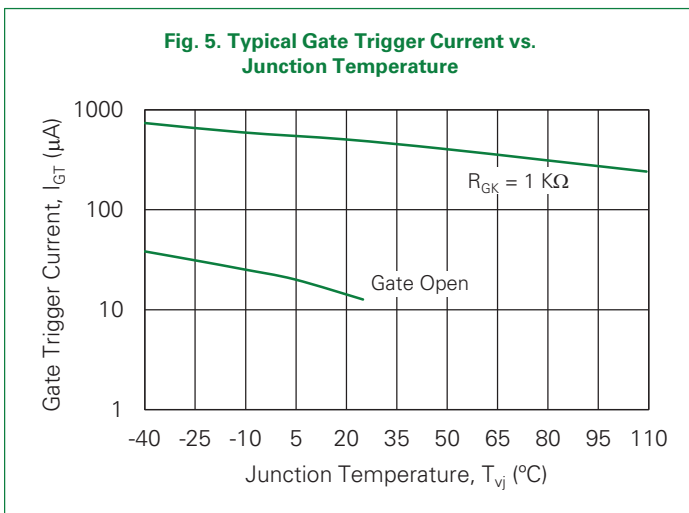
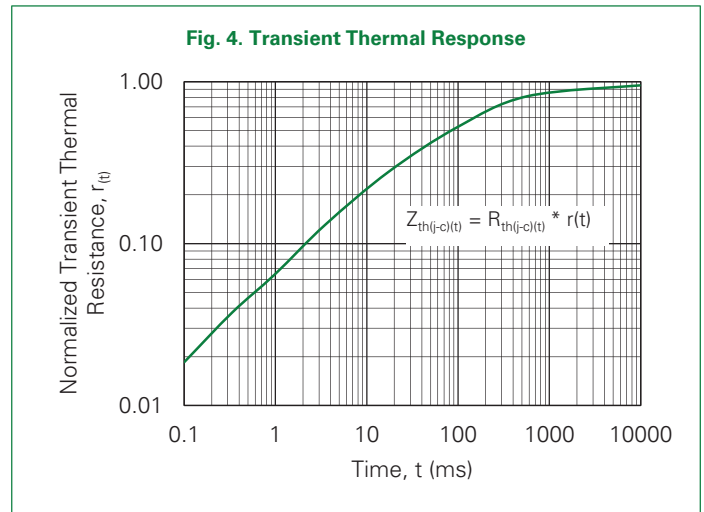
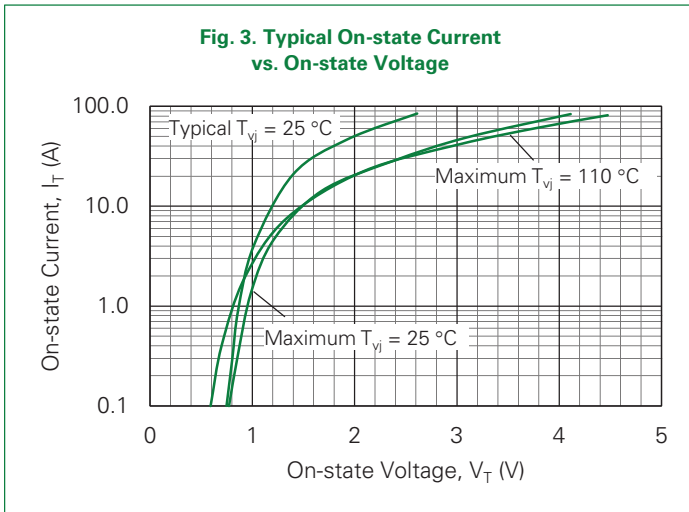
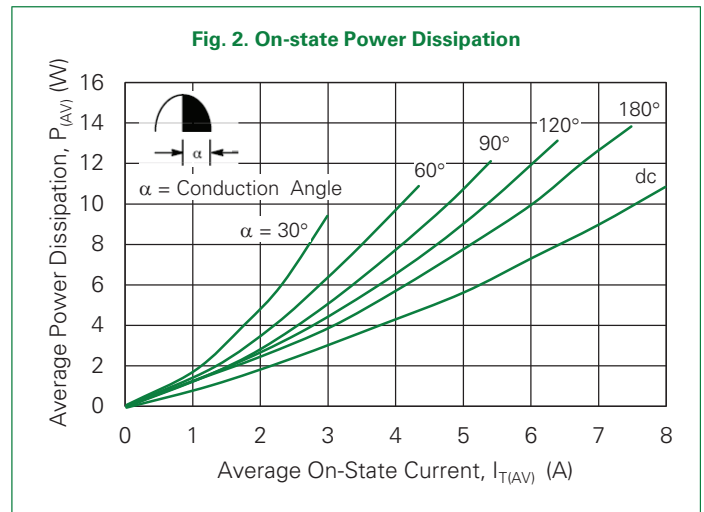
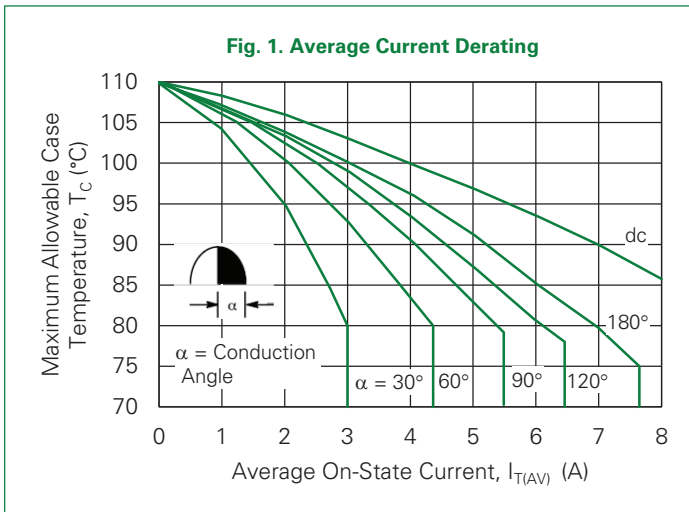
Symbol	Characteristics	Conditions	Value			Units
			Min.	Typ.	Max.	
dv/dt	Critical Rate of Rise of Off-State Voltage	$V_D = 0.67 \times \text{Rated } V_{DRM}$ , Exponential Waveform, 100 ohm, $T_{vj} = 110^\circ\text{C}$	37	45	–	V/ $\mu\text{s}$
di/dt	Critical Rate of Rise of On-State Current	$I_{PK} = 50 \text{ A}$ , $P_W = 40 \text{ sec}$ , $diG/dt = 1 \text{ A/sec}$ , $I_{GT} = 10 \text{ mA}$	–	50	100	A/ $\mu\text{s}$

## Voltage Current Characteristics of SCR

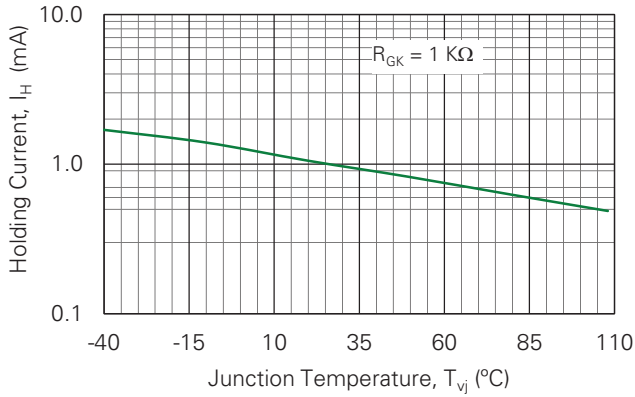
Symbol	Characteristics
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
$I_{DRM}$	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
$I_{RRM}$	Peak Reverse Blocking Current
$V_{TM}$	Maximum On-state Voltage
$I_H$	Holding Current



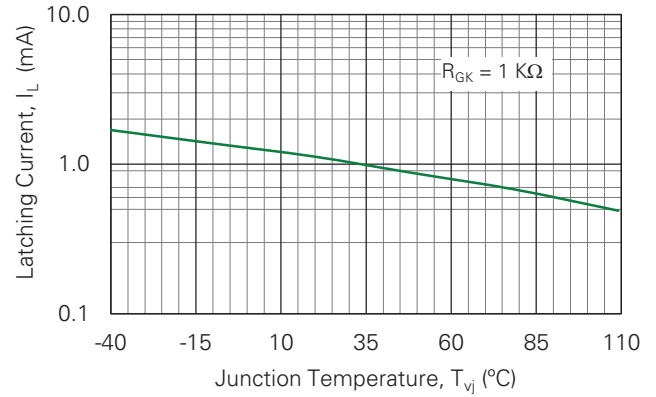
**Characteristic Curves**



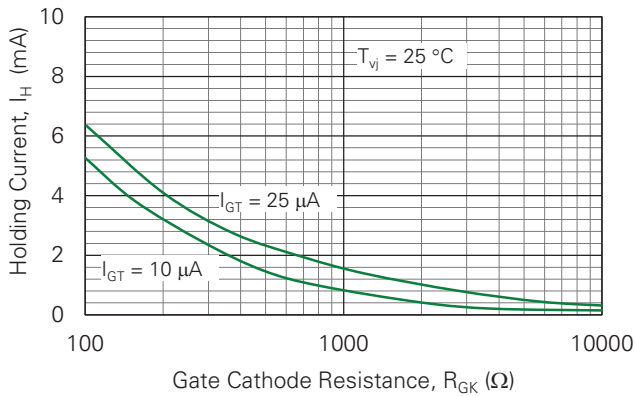
**Fig. 7. Typical Holding Current vs. Junction Temperature**



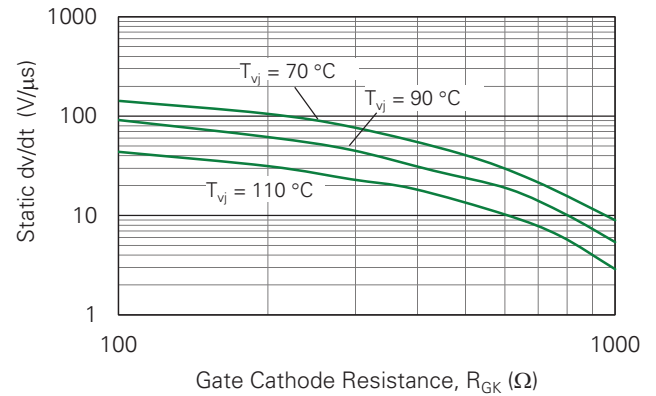
**Fig. 8. Typical Latching Current vs. Junction Temperature**



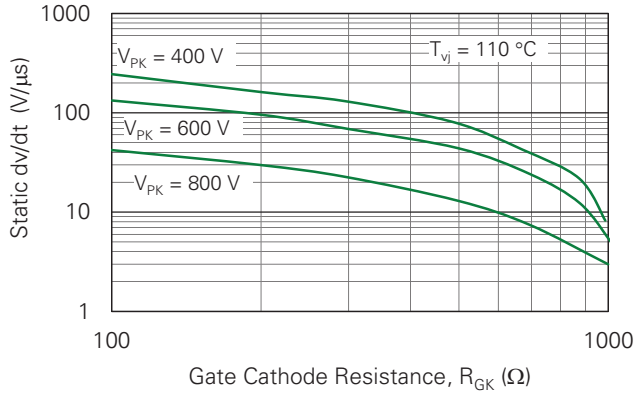
**Fig. 9. Holding Current vs. Gate-Cathode Resistance**



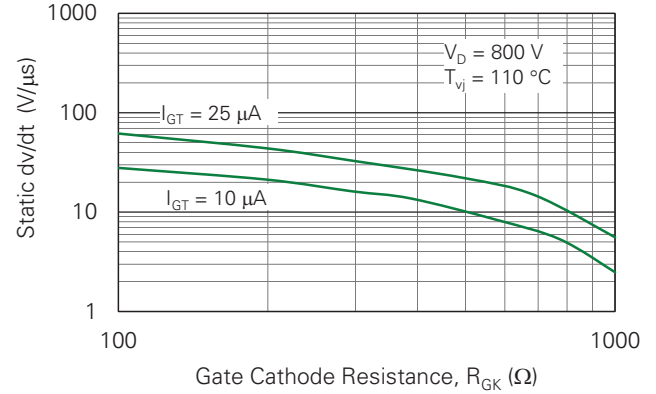
**Fig. 10. Exponential Static dv/dt vs. Gate-Cathode Resistance and Junction Temperature**



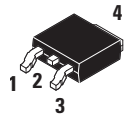
**Fig. 11. Typical Gate Trigger Current vs. Junction Temperature**



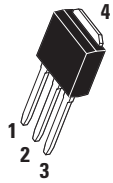
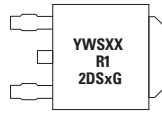
**Fig. 12. Typical Gate Trigger Voltage vs. Junction Temperature**



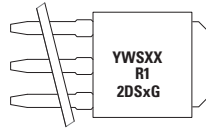
**Part Marking**



**DPAK-3**  
Case 369C  
Style 4



**IPAK-3**  
Case 369D  
Style 4

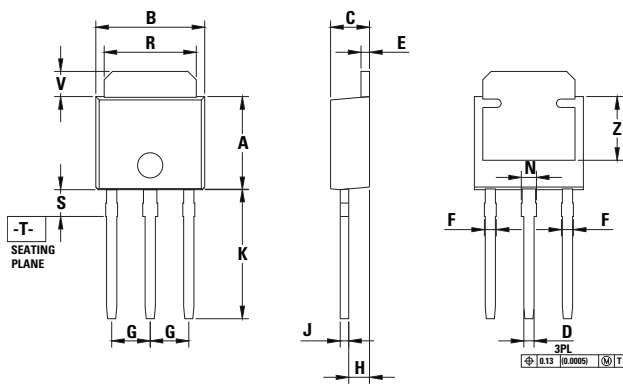


**Packing Options**

Part Number	Package Type	Packing Mode	Base Quantity
MCR12DSMT4G	DPAK	Tape and Reel	2500
MCR12DSN-1G	IPAK	Box	4000
MCR12DSNT4G	DPAK	Tape and Reel	2500

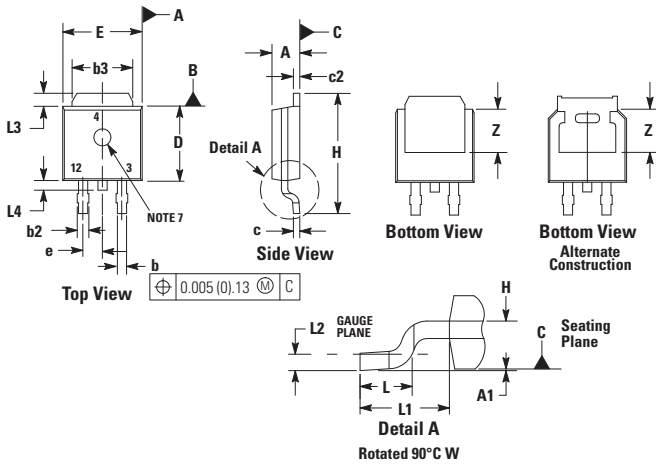
**Package Dimensions** TO-251 (IPAK-3)

**TO251-3L POD**

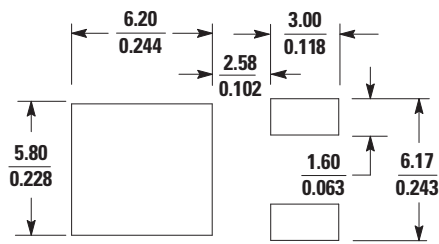


Symbol	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	5.40	5.70	0.213	0.224
B	6.40	6.60	0.252	0.260
C	2.20	2.40	0.087	0.094
D	0.60	0.75	0.024	0.030
E	0.55	0.65	0.022	0.026
F	0.58	0.78	0.022	0.030
G	2.30		0.091	
H	1.18	1.28	0.046	0.050
J	0.49	0.59	0.019	0.023
K	7.40	8.00	0.291	0.315
N	0.78	0.98	0.031	0.038
R	5.30	5.50	0.209	0.217
S	1.60		0.063	
V	1.35	1.65	0.053	0.065
Z	3.80		0.150	

**Package Dimensions** TO-252 (DPAK-3)



Soldering Footprint



SCALE 3:1  $\left(\frac{\text{mm}}{\text{inches}}\right)$

Symbol	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.40	0.087	0.094
A1	0.00	0.12	0.000	0.005
b	0.55	0.75	0.022	0.030
b2	0.65	0.85	0.026	0.033
b3	5.30	5.50	0.209	0.217
C	0.49	0.59	0.019	0.023
c2	0.49	0.59	0.019	0.023
D	5.40	5.70	0.213	0.224
E	6.40	6.60	0.252	0.260
e	2.30		0.091	
H	9.50	10.30	0.374	0.406
L	1.47	1.78	0.058	0.070
L1	2.90		0.114	
L2	0.49	0.59	0.019	0.023
L3	1.35	1.65	0.053	0.065
L4	0.70	1.00	0.028	0.039
Z	3.90	-	0.154	-

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Part of:

